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Dual General Purpose Transistor

The NST3904DP6T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-963 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 100-300
- Low $V_{CE(sat)}$, $\leq 0.4 \text{ V}$
- Reduces Board Space and Component Count
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CEO}	40	Vdc
Collector - Base Voltage		V _{CBO}	60	Vdc
Emitter - Base Voltage		V _{EBO}	6.0	Vdc
Collector Current - Continuous		I _C	200	mAdc
Electrostatic Discharge	HBM MM	ESD Class	2 B	

THERMAL CHARACTERISTICS

Characteristic (Single Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 1)	P _D	240 1.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	520	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 2)	P _D	280 2.2	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	446	°C/W
Characteristic (Dual Heated) (Note 3)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 1)	P _D	350 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	357	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 2)	P _D	420 3.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	297	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

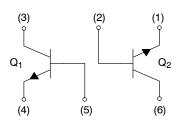
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 @ 100 mm², 1 oz. copper traces, still air. 2. FR-4 @ 500 mm², 1 oz. copper traces, still air.
- 3. Dual heated values assume total power is sum of two equally powered channels.



ON Semiconductor®

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NST3904DP6T5G



SOT-963 CASE 527AD

MARKING DIAGRAM



= Device Code = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NST3904DP6T5G	SOT-963 (Pb-Free)	8000/Tape & Reel
NSVT3904DP6T5G	SOT-963 (Pb-Free)	8000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	•	•
Collector – Emitter Breakdown Voltage (Note 4) (I _C = 1.0 mAdc, I _B = 0)		V _{(BR)CEO}	40	-	Vdc
Collector - Base Breakdown Voltag	ge (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	-	Vdc
Emitter - Base Breakdown Voltage	(I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	-	Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{CEX}	-	50	nAdc
ON CHARACTERISTICS (Note 4)		•		•	1
		h _{FE}	40 70 100 60 30	- 300 - -	-
Collector – Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc)		V _{CE(sat)}	- -	0.2 0.3	Vdc
Base – Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc)		V _{BE(sat)}	0.65 -	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERIS	STICS				
Current – Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)		f _T	200	-	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	-	4.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	-	8.0	pF
Noise Figure (V_{CE} = 5.0 Vdc, I_{C} = 100 μ Adc, R_{S} = 1.0 k Ω , f = 1.0 kHz)		NF	-	5.0	dB
SWITCHING CHARACTERISTICS	3	•			
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc})$	t _d	_	35	
Rise Time	(I _C = 10 mAdc, I _{B1} = 1.0 mAdc)	t _r	_	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_C = 10 \text{ mAdc})$	t _s	-	275	
Fall Time	$(I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	t _f	-	50	ns

^{4.} Pulse Test: Pulse Width \leq 300 $\mu s;$ Duty Cycle \leq 2.0%.

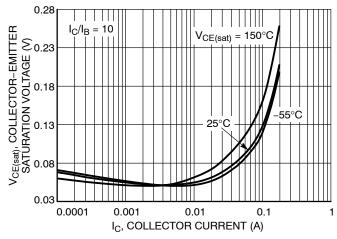


Figure 1. Collector Emitter Saturation Voltage vs.
Collector Current

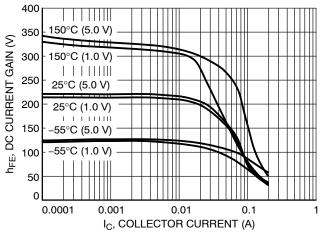


Figure 2. DC Current Gain vs. Collector Current

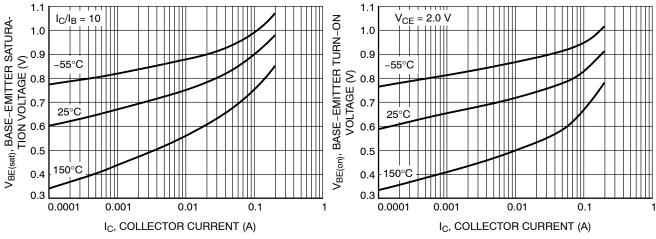


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

Figure 4. Base Emitter Turn-On Voltage vs.
Collector Current

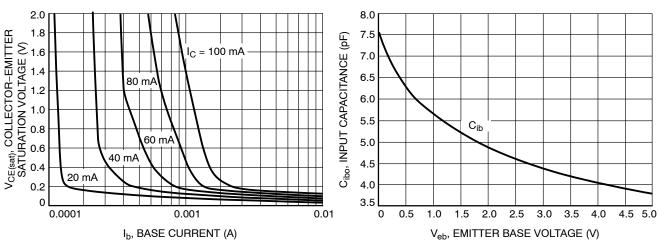


Figure 5. Saturation Region

Figure 6. Input Capacitance

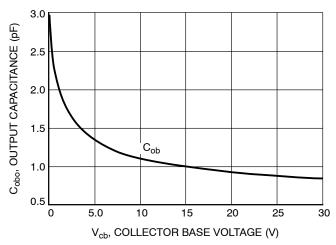
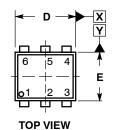
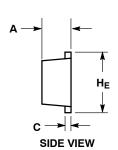


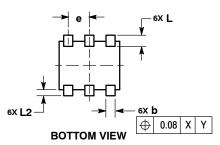
Figure 7. Output Capacitance

PACKAGE DIMENSIONS

SOT-963 CASE 527AD **ISSUE E**





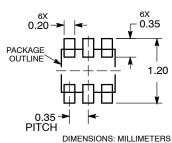


NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.34	0.37	0.40	
b	0.10	0.15	0.20	
С	0.07	0.12	0.17	
D	0.95	1.00	1.05	
E	0.75	0.80	0.85	
е	0.35 BSC			
Hε	0.95	1.00	1.05	
L	0.19 REF			
L2	0.05	0.10	0.15	

RECOMMENDED MOUNTING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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